

isc Silicon NPN Power Transistor

BUT70W

DESCRIPTION

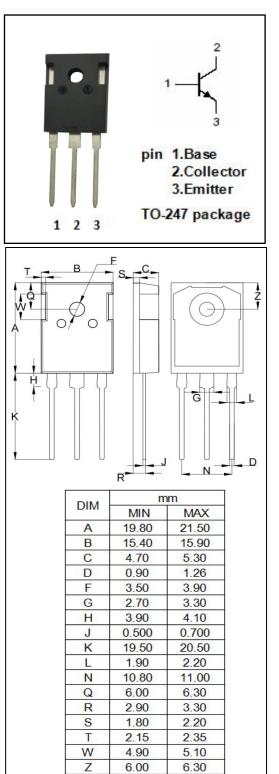
- High Current Capability
- Very Low Saturation Voltage and High Gain
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

• Designed for switching regulation、 motor control and High frequency and efficiency converters.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)							
PARAMETER	ALUE	UNIT					
Collector-Emitter Voltage		125	v				
Emitter-Base Voltage		7	V				
Collector Current- Continuous		40	А				
Collector Current-Peak		120	A				
Base Current- Continuous		8	A				
Base Current-Peak		24	А				
Collector Power Dissipation @ T _C =25°C		200	W				
Junction Temperature		150	°C				
Storage Temperature Range	-6	5~150	°C				
PARAMETER	МАХ	UNIT					
Thermal Resistance,Junction to Ca	0.63	°C/W					
	PARAMETER Collector-Emitter Voltage Emitter-Base Voltage Collector Current- Continuous Collector Current-Peak Base Current- Continuous Base Current-Peak Collector Power Dissipation @ Tc=25°C Junction Temperature Storage Temperature Range	PARAMETER V. Collector-Emitter Voltage Image: Collector Emitter-Base Voltage Image: Collector Current- Continuous Collector Current-Peak Image: Collector Current-Peak Image: Collector Power Dissipation Base Current-Peak Image: Collector Power Dissipation Image: Collector Power Dissipation Junction Temperature Image: Collector Power Dissipation Image: Collector Power Dissipation Base Temperature Range Image: Collector Power Power Power Power Power Power Power Image: Collector Power Power Collector Power Dissipation Image: Collector Power Power Image: Collector Power Storage Temperature Range Image: Collector Power Image: Collector Power	PARAMETERVALUECollector-Emitter Voltage125Emitter-Base Voltage7Collector Current- Continuous40Collector Current-Peak120Base Current- Continuous8Base Current-Peak24Collector Power Dissipation @ Tc=25°C200Junction Temperature150Storage Temperature Range-65~150PARAMETERMAX				



isc website: <u>www.iscsemi.com</u>

¹ *isc & iscsemi* is registered trademark 2023-2-1



isc Silicon NPN Power Transistor

BUT70W

ELECTRICAL CHARACTERISTICS

 $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	Ic= 50mA ; Iв= 0	125			V
V _{CE(sat)} -1	Collector-Emitter Saturation Voltage	Ι _C = 70Α; Ι _Β = 7Α			0.9	V
V _{CE(sat)} -2	Collector-Emitter Saturation Voltage	I _C = 35A; I _B =1.75A			0.9	V
V _{BE(sat)} -1	Base-Emitter Saturation Voltage	I _C =70A; I _B = 7A			1.8	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	I _C =35A; I _B = 1.75A			1.4	V
І _{ЕВО}	Emitter Cutoff Current	V _{EB} = 5.0V ; I _C = 0			1	mA

Switching times

t _{stg}	Storage Time		- I _C = 35A , I _{B1} = 1.75A; L _B = 150 μ Η	1.8	μs
t _f	Fall Time			0.2	μs

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications. ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.